Kimberly A Dick

List of Publications by Year
in descending order

182 papers	10,244 citations	36303 51 h-index	37204 96 g-index
186 all docs	186 docs citations	186 times ranked	7349 citing authors

#	Article	IF	Citations
1	Controlled polytypic and twin-plane superlattices in iiiâ€“v nanowires. Nature Nanotechnology, 2009, 4, 50-55.	31.5	646
2	Synthesis of branched 'nanotrees' by controlled seeding of multiple branching events. Nature Materials, 2004, 3, 380-384.	27.5	592
3	Size-Dependent Melting of Silica-Encapsulated Gold Nanoparticles. Journal of the American Chemical Society, 2002, 124, 2312-2317.	13.7	515
4	Preferential Interface Nucleation: An Expansion of the VLS Growth Mechanism for Nanowires. Advanced Materials, 2009, 21, 153-165.	21.0	309
5	Failure of the Vaporâ˘'Liquidâ˘'Solid Mechanism in Au-Assisted MOVPE Growth of InAs Nanowires. Nano Letters, 2005, 5, 761-764.	9.1	282
6	Growth of one-dimensional nanostructures in MOVPE. Journal of Crystal Growth, 2004, 272, 211-220.	1.5	278
7	Interface dynamics and crystal phase switching in GaAs nanowires. Nature, 2016, 531, 317-322.	27.8	272
8	A review of nanowire growth promoted by alloys and non-alloying elements with emphasis on Au-assisted IIIâ€“V nanowires. Progress in Crystal Growth and Characterization of Materials, 2008, 54, 138-173.	4.0	249
9	Crystal Phase Engineering in Single InAs Nanowires. Nano Letters, 2010, 10, 3494-3499.	9.1	234
10	Control of IIIâ€“V nanowire crystal structure by growth parameter tuning. Semiconductor Science and Technology, 2010, 25, 024009.	2.0	219
11	Effects of Crystal Phase Mixing on the Electrical Properties of InAs Nanowires. Nano Letters, 2011, 11, 2424-2429.	9.1	211
12	The Morphology of Axial and Branched Nanowire Heterostructures. Nano Letters, 2007, 7, 1817-1822.	9.1	175
13	Semiconductor nanowires for 0D and 1D physics and applications. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 25, 313-318.	2.7	172
14	InAs/GaSb Heterostructure Nanowires for Tunnel Field-Effect Transistors. Nano Letters, 2010, 10, 4080-4085.	9.1	161
15	Highâ€Quality InAs/InSb Nanowire Heterostructures Grown by Metalâ€“Organic Vaporâ€Phase Epitaxy. Small, 2008, 4, 878-882.	10.0	160
16	A General Approach for Sharp Crystal Phase Switching in InAs, GaAs, InP, and GaP Nanowires Using Only Group V Flow. Nano Letters, 2013, 13, 4099-4105.	9.1	156
17	Gold-free growth of GaAs nanowires on silicon: arrays and polytypism. Nanotechnology, 2010, 21, 385602.	2.6	149
18	Effects of Supersaturation on the Crystal Structure of Gold Seeded IIIâ˘'V Nanowires. Crystal Growth and Design, 2009, 9, 766-773.	3.0	147

#	Article	IF	Citations
19	A New Understanding of Au-Assisted Growth of III-V Semiconductor Nanowires. Advanced Functional Materials, 2005, 15, 1603-1610.	14.9	139
20	Diameter Dependence of the Wurtziteâˆ’Zinc Blende Transition in InAs Nanowires. Journal of Physical Chemistry C, 2010, 114, 3837-3842.	3.1	129
21	InSb heterostructure nanowires: MOVPE growth under extreme lattice mismatch. Nanotechnology, 2009, 20, 495606.	2.6	121
22	Controlling the Abruptness of Axial Heterojunctions in IIIâ€“V Nanowires: Beyond the Reservoir Effect. Nano Letters, 2012, 12, 3200-3206.	9.1	121
23	Unit Cell Structure of Crystal Polytypes in InAs and InSb Nanowires. Nano Letters, 2011, 11, 1483-1489.	9.1	117
24	High-Current GaSb/InAs(Sb) Nanowire Tunnel Field-Effect Transistors. IEEE Electron Device Letters, 2013, 34, 211-213.	3.9	108
25	Large Thermoelectric Power Factor Enhancement Observed in InAs Nanowires. Nano Letters, 2013, 13, 4080-4086.	9.1	107
26	High Current Density Esaki Tunnel Diodes Based on GaSb-InAsSb Heterostructure Nanowires. Nano Letters, 2011, 11, 4222-4226.	9.1	106
27	Recent advances in semiconductor nanowire heterostructures. CrystEngComm, 2011, 13, 7175.	2.6	104
28	Growth related aspects of epitaxial nanowires. Nanotechnology, 2006, 17, S355-S361.	2.6	100
29	Thermal conductivity of indium arsenide nanowires with wurtzite and zinc blende phases. Physical Review B, 2011, 83, .	3.2	96
30	Faceting, composition and crystal phase evolution in IIIâ€“V antimonide nanowire heterostructures revealed by combining microscopy techniques. Nanotechnology, 2012, 23, 095702.	2.6	95
31	Precursor evaluation for<i>in situ</i>InP nanowire doping. Nanotechnology, 2008, 19, 445602.	2.6	92
32	Atomic-Scale Variability and Control of III-V Nanowire Growth Kinetics. Science, 2014, 343, 281-284.	12.6	87
33	The electrical and structural properties of n-type InAs nanowires grown from metalâ€“organic precursors. Nanotechnology, 2010, 21, 205703.	2.6	86
34	Position-Controlled Interconnected InAs Nanowire Networks. Nano Letters, 2006, 6, 2842-2847.	9.1	85
35	GaAs/GaSb nanowire heterostructures grown by MOVPE. Journal of Crystal Growth, 2008, 310, 4115-4121.	1.5	85
36	Gold-free GaAs/GaAsSb heterostructure nanowires grown on silicon. Applied Physics Letters, 2010, 96, .	3.3	83

#	Article	IF	Citations
37	Electronic and Structural Differences between Wurtzite and Zinc Blende InAs Nanowire Surfaces: Experiment and Theory. ACS Nano, 2014, 8, 12346-12355.	14.6	78
38	Metal-seeded growth of IIIâ€"V semiconductor nanowires: towards gold-free synthesis. Nanoscale, 2014, 6, 3006-3021.	5.6	78
39	Optimization of Au-assisted InAs nanowires grown by MOVPE. Journal of Crystal Growth, 2006, 297, 326-333.	1.5	67
40	Direct Imaging of Atomic Scale Structure and Electronic Properties of GaAs Wurtzite and Zinc Blende Nanowire Surfaces. Nano Letters, 2013, 13, 4492-4498.	9.1	63
41	Strategies To Control Morphology in Hybrid Group IIIâ€"V/Group IV Heterostructure Nanowires. Nano Letters, 2013, 13, 903-908.	9.1	63
42	Surface-enhanced Raman scattering of rhodamine 6G on nanowire arrays decorated with gold nanoparticles. Nanotechnology, 2008, 19, 275712.	2.6	62
43	Confinement in Thickness-Controlled GaAs Polytype Nanodots. Nano Letters, 2015, 15, 2652-2656.	9.1	62
44	The use of gold for fabrication of nanowire structures. Gold Bulletin, 2009, 42, 172-181.	2.7	61
45	High-Performance InAs Nanowire MOSFETs. IEEE Electron Device Letters, 2012, 33, 791-793.	3.9	60
46	Observation of type-II recombination in single wurtzite/zinc-blende GaAs heterojunction nanowires. Physical Review B, 2014, 89, .	3.2	60
47	Combinatorial Approaches to Understanding Polytypism in IIIâ€"V Nanowires. ACS Nano, 2012, 6, 6142-6149.	14.6	59
48	Enhanced Sb incorporation in InAsSb nanowires grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2011, 98, .	3.3	56
49	Electrical properties of InAs1â^'xSbx and InSb nanowires grown by molecular beam epitaxy. Applied Physics Letters, 2012, 100, 232105.	3.3	56
50	High quality InAs and GaSb thin layers grown on Si (111). Journal of Crystal Growth, 2011, 332, 12-16.	1.5	54
51	Generation of size-selected gold nanoparticles by spark discharge â€" for growth of epitaxial nanowires. Gold Bulletin, 2009, 42, 20-26.	2.7	51
52	High crystal quality wurtzite-zinc blende heterostructures in metal-organic vapor phase epitaxy-grown GaAs nanowires. Nano Research, 2012, 5, 470-476.	10.4	51
53	Growth of InAs/InP coreâ€"shell nanowires with various pure crystal structures. Nanotechnology, 2012, 23, 285601.	2.6	50
54	In situ analysis of catalyst composition during gold catalyzed GaAs nanowire growth. Nature Communications, 2019, 10, 4577.	12.8	49

#	Article	IF	Citations
55	Wurtziteâ€“zincblende superlattices in InAs nanowires using a supply interruption method. Nanotechnology, 2011, 22, 265606.	2.6	46
56	Growth of GaP nanotree structures by sequential seeding of 1D nanowires. Journal of Crystal Growth, 2004, 272, 131-137.	1.5	45
57	Characterization of GaSb nanowires grown by MOVPE. Journal of Crystal Growth, 2008, 310, 5119-5122.	1.5	45
58	Crystal structure control in Au-free self-seeded InSb wire growth. Nanotechnology, 2011, 22, 145603.	2.6	45
59	Diameter Limitation in Growth of III-Sb-Containing Nanowire Heterostructures. ACS Nano, 2013, 7, 3668-3675.	14.6	45
60	Single-electron transport in InAs nanowire quantum dots formed by crystal phase engineering. Physical Review B, 2016, 93, .	3.2	45
61	Demonstration of Defect-Free and Composition Tunable Ga_{<i>x</i>}In_{1â€“<i>x</i>}Sb Nanowires. Nano Letters, 2012, 12, 4914-4919.	9.1	44
62	A comparative study of the effect of gold seed particle preparation method on nanowire growth. Nano Research, 2010, 3, 506-519.	10.4	43
63	Parameter space mapping of InAs nanowire crystal structure. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 04D103.	1.2	43
64	Carrier control and transport modulation in GaSb/InAsSb core/shell nanowires. Applied Physics Letters, 2012, 101, .	3.3	43
65	Crystal phase control in GaAs nanowires: opposing trends in the Ga- and As-limited growth regimes. Nanotechnology, 2015, 26, 301001.	2.6	43
66	Selective GaSb radial growth on crystal phase engineered InAs nanowires. Nanoscale, 2015, 7, 10472-10481.	5.6	42
67	Understanding the 3D structure of mathrm {GaAslangle 111angle B} nanowires. Nanotechnology, 2007, 18, 485717.	2.6	41
68	Directed Growth of Branched Nanowire Structures. MRS Bulletin, 2007, 32, 127-133.	3.5	40
69	Control of composition and morphology in InGaAs nanowires grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2013, 383, 158-165.	1.5	39
70	Magnetic-Field-Independent Subgap States in Hybrid Rashba Nanowires. Physical Review Letters, 2020, 125, 017701.	7.8	38
71	Uniform and position-controlled InAs nanowires on 2â€²â€²Si substrates for transistor applications. Nanotechnology, 2012, 23, 015302.	2.6	36
72	Improving InAs nanotree growth with composition-controlled Auâ€“In nanoparticles. Nanotechnology, 2006, 17, 1344-1350.	2.6	35

#	Article	IF	Citations
73	Control of GaP and GaAs Nanowire Morphology through Particle and Substrate Chemical Modification. Nano Letters, 2008, 8, 4087-4091.	9.1	35
74	Tip-enhanced Raman scattering of p-thiocresol molecules on individual gold nanoparticles. Applied Physics Letters, 2008, 92, 093110.	3.3	35
75	Formation of the Axial Heterojunction in GaSb/InAs(Sb) Nanowires with High Crystal Quality. Crystal Growth and Design, 2011, 11, 4588-4593.	3.0	35
76	Electrical and Surface Properties of InAs/InSb Nanowires Cleaned by Atomic Hydrogen. Nano Letters, 2015, 15, 4865-4875.	9.1	35
77	Conduction Band Offset and Polarization Effects in InAs Nanowire Polytype Junctions. Nano Letters, 2017, 17, 902-908.	9.1	34
78	InAs nanowires grown by MOVPE. Journal of Crystal Growth, 2007, 298, 631-634.	1.5	33
79	Influence of doping on the electronic transport in GaSb/InAs(Sb) nanowire tunnel devices. Applied Physics Letters, 2012, 101, 043508.	3.3	33
80	Silver as Seed-Particle Material for GaAs Nanowiresâ€"Dictating Crystal Phase and Growth Direction by Substrate Orientation. Nano Letters, 2016, 16, 2181-2188.	9.1	33
81	Electrical properties of GaSb/InAsSb core/shell nanowires. Nanotechnology, 2014, 25, 425201.	2.6	32
82	Hydrogen-assisted spark discharge generated metal nanoparticles to prevent oxide formation. Aerosol Science and Technology, 2018, 52, 347-358.	3.1	31
83	Independent Control of Nucleation and Layer Growth in Nanowires. ACS Nano, 2020, 14, 3868-3875.	14.6	31
84	Electrospraying of colloidal nanoparticles for seeding of nanostructure growth. Nanotechnology, 2007, 18, 105304.	2.6	29
85	Spectroscopy of the superconducting proximity effect in nanowires using integrated quantum dots. Communications Physics, 2019, 2, .	5.3	28
86	Phase Transformation in Radially Merged Wurtzite GaAs Nanowires. Crystal Growth and Design, 2015, 15, 4795-4803.	3.0	27
87	Parallel-Coupled Quantum Dots in InAs Nanowires. Nano Letters, 2017, 17, 7847-7852.	9.1	27
88	Simulation of GaAs Nanowire Growth and Crystal Structure. Nano Letters, 2019, 19, 1197-1203.	9.1	27
89	Crystal Phase-Dependent Nanophotonic Resonances in InAs Nanowire Arrays. Nano Letters, 2014, 14, 5650-5655.	9.1	26
90	Simultaneous growth mechanisms for Cu-seeded InP nanowires. Nano Research, 2012, 5, 297-306.	10.4	25

#	Article	IF	Citations
91	Sn-Seeded GaAs Nanowires as Self-Assembled Radial <i>pâ€“n</i> Junctions. Nano Letters, 2015, 15, 3757-3762.	9.1	25
92	Nondestructive Complete Mechanical Characterization of Zinc Blende and Wurtzite GaAs Nanowires Using Time-Resolved Pumpâ€“Probe Spectroscopy. Nano Letters, 2016, 16, 4792-4798.	9.1	25
93	Enhanced sputtering and incorporation of Mn in implanted GaAs and ZnO nanowires. Journal Physics D: Applied Physics, 2014, 47, 394003.	2.8	24
94	Polarity and growth directions in Sn-seeded GaSb nanowires. Nanoscale, 2017, 9, 3159-3168.	5.6	24
95	Atomic Scale Surface Structure and Morphology of InAs Nanowire Crystal Superlattices: The Effect of Epitaxial Overgrowth. ACS Applied Materials & Interfaces, 2015, 7, 5748-5755.	8.0	23
96	Wurtzite GaAs Quantum Wires: One-Dimensional Subband Formation. Nano Letters, 2016, 16, 2774-2780.	9.1	23
97	Polytype Attainability in IIIâ€“V Semiconductor Nanowires. Crystal Growth and Design, 2016, 16, 371-379.	3.0	23
98	Direct nucleation, morphology and compositional tuning of InAs_{1â^'<i>x</i>}Sb<i>_x</i>nanowires on InAs (111) B substrates. Nanotechnology, 2017, 28, 165601.	2.6	23
99	Self-catalyzed MBE grown GaAs/GaAs_{<i>x</i>}Sb_{1â^'<i>x</i>}coreâ€“shell nanowires in ZB and WZ crystal structures. Nanotechnology, 2013, 24, 405601.	2.6	21
100	Atomic-Resolution Spectrum Imaging of Semiconductor Nanowires. Nano Letters, 2018, 18, 1557-1563.	9.1	21
101	Can antimonide-based nanowires form wurtzite crystal structure?. Nanoscale, 2016, 8, 2778-2786.	5.6	20
102	In situ metal-organic chemical vapour deposition growth of IIIâ€“V semiconductor nanowires in the Lund environmental transmission electron microscope. Semiconductor Science and Technology, 2020, 35, 034004.	2.0	20
103	Semiconductor nanostructures enabled by aerosol technology. Frontiers of Physics, 2014, 9, 398-418.	5.0	19
104	Morphology and composition controlled Ga_xIn_{1â^'x}Sb nanowires: understanding ternary antimonide growth. Nanoscale, 2014, 6, 1086-1092.	5.6	19
105	Microphotoluminescence studies of tunable wurtziteInAs0.85P0.15quantum dots embedded in wurtzite InP nanowires. Physical Review B, 2009, 80, .	3.2	18
106	Kinetics of Auâ€“Ga Droplet Mediated Decomposition of GaAs Nanowires. Nano Letters, 2019, 19, 3498-3504.	9.1	18
107	Unraveling the Ultrafast Hot Electron Dynamics in Semiconductor Nanowires. ACS Nano, 2021, 15, 1133-1144.	14.6	18
108	Epitaxial InP nanowire growth from Cu seed particles. Journal of Crystal Growth, 2011, 315, 134-137.	1.5	17

#	Article	IF	Citations
109	Highly controlled InAs nanowires on Si(111) wafers by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 206-209.	0.8	17
110	Efficient and continuous microwave photoconversion in hybrid cavity-semiconductor nanowire double quantum dot diodes. Nature Communications, 2021, 12, 5130.	12.8	17
111	Conductance Enhancement of InAs/InP Heterostructure Nanowires by Surface Functionalization with Oligo(phenylene vinylene)s. ACS Nano, 2013, 7, 4111-4118.	14.6	16
112	Time-Resolved X-ray Diffraction Investigation of the Modified Phonon Dispersion in InSb Nanowires. Nano Letters, 2014, 14, 541-546.	9.1	16
113	Scanning Tunneling Spectroscopy on InAsâ€"GaSb Esaki Diode Nanowire Devices during Operation. Nano Letters, 2015, 15, 3684-3691.	9.1	16
114	Electron-hole interactions in coupled InAs-GaSb quantum dots based on nanowire crystal phase templates. Physical Review B, 2016, 94, .	3.2	16
115	Temperature dependent electronic band structure of wurtzite GaAs nanowires. Nanoscale, 2018, 10, 1481-1486.	5.6	16
116	Vaporâ€"solidâ€"solid growth dynamics in GaAs nanowires. Nanoscale Advances, 2021, 3, 5928-5940.	4.6	16
117	Effects of growth conditions on the crystal structure of gold-seeded GaP nanowires. Journal of Crystal Growth, 2008, 310, 5102-5105.	1.5	15
118	High resolution scanning gate microscopy measurements on InAs/GaSb nanowire Esaki diode devices. Nano Research, 2014, 7, 877-887.	10.4	15
119	Characterization of Ambipolar GaSb/InAs Coreâ€"Shell Nanowires by Thermovoltage Measurements. ACS Nano, 2015, 9, 7033-7040.	14.6	15
120	Electronic Structure Changes Due to Crystal Phase Switching at the Atomic Scale Limit. ACS Nano, 2017, 11, 10519-10528.	14.6	15
121	Height-controlled nanowire branches on nanotrees using a polymer mask. Nanotechnology, 2007, 18, 035601.	2.6	14
122	Control and understanding of kink formation in InAsâ€"InP heterostructure nanowires. Nanotechnology, 2013, 24, 345601.	2.6	14
123	InAs nanowire GAA n-MOSFETs with 12â€"15 nm diameter. , 2016, , .		14
124	Schottky barrier and contact resistance of InSb nanowire field-effect transistors. Nanotechnology, 2016, 27, 275204.	2.6	14
125	Crystal Structure Induced Preferential Surface Alloying of Sb on Wurtzite/Zinc Blende GaAs Nanowires. Nano Letters, 2017, 17, 3634-3640.	9.1	14
126	Tuning the Two-Electron Hybridization and Spin States in Parallel-Coupled InAs Quantum Dots. Physical Review Letters, 2018, 121, 156802.	7.8	14

#	Article	IF	Citations
127	Limits of IIIâ€“V Nanowire Growth Based on Droplet Dynamics. Journal of Physical Chemistry Letters, 2020, 11, 2949-2954.	4.6	14
128	Diameter reduction of nanowire tunnel heterojunctions using in situ annealing. Applied Physics Letters, 2011, 99, 203101.	3.3	13
129	Zincblendeâ€toâ€wurtzite interface improvement by group III loading in Auâ€seeded GaAs nanowires. Physica Status Solidi - Rapid Research Letters, 2013, 7, 855-859.	2.4	13
130	Realization of Wurtzite GaSb Using InAs Nanowire Templates. Advanced Functional Materials, 2018, 28, 1800512.	14.9	13
131	Simultaneous Growth of Pure Wurtzite and Zinc Blende Nanowires. Nano Letters, 2019, 19, 2723-2730.	9.1	13
132	CRYSTAL STRUCTURE OF BRANCHED EPITAXIAL IIIâ€“V NANOTREES. Nano, 2006, 01, 139-151.	1.0	12
133	Compositional Correlation between the Nanoparticle and the Growing Au-Assisted In_{<i>x</i>}Ga_{1â€“<i>x</i>}As Nanowire. Journal of Physical Chemistry Letters, 2021, 12, 7590-7595.	4.6	12
134	Experimental Verification of the Work Fluctuation-Dissipation Relation for Information-to-Work Conversion. Physical Review Letters, 2022, 128, 040602.	7.8	12
135	Demonstration of Sn-seeded GaSb homo- and GaAsâ€“GaSb heterostructural nanowires. Nanotechnology, 2016, 27, 175602.	2.6	11
136	Annealing of Au, Ag and Auâ€“Ag alloy nanoparticle arrays on GaAs (100) and (111)B. Nanotechnology, 2017, 28, 205702.	2.6	11
137	Thermodynamic Stability of Gold-Assisted InAs Nanowire Growth. Journal of Physical Chemistry C, 2017, 121, 21678-21684.	3.1	11
138	Spatial Control of Multiphoton Electron Excitations in InAs Nanowires by Varying Crystal Phase and Light Polarization. Nano Letters, 2018, 18, 907-915.	9.1	11
139	Branched InAs nanowire growth by droplet confinement. Applied Physics Letters, 2018, 113, 123104.	3.3	11
140	Enabling <i>In Situ</i> Studies of Metal-Organic Chemical Vapor Deposition in a Transmission Electron Microscope. Microscopy and Microanalysis, 2022, 28, 1484-1492.	0.4	11
141	Highâ€Speed Nanometerâ€Scale Imaging for Studies of Nanowire Mechanics. Small, 2007, 3, 1699-1702.	10.0	10
142	Targeted deposition of Au aerosol nanoparticles on vertical nanowires for the creation of nanotrees. Journal of Nanoparticle Research, 2007, 9, 1211-1216.	1.9	10
143	Branched nanotrees with immobilized acetylcholine esterase for nanobiosensor applications. Nanotechnology, 2010, 21, 055102.	2.6	10
144	Palladium seeded GaAs nanowires. Journal of Materials Research, 2016, 31, 175-185.	2.6	10

#	Article	IF	Citations
145	Interface Dynamics in Agâ€"Cu₃P Nanoparticle Heterostructures. Journal of the American Chemical Society, 2022, 144, 248-258.	13.7	10
146	Crystal structure tuning in GaAs nanowires using HCl. Nanoscale, 2014, 6, 8257.	5.6	9
147	Characterization of individual stacking faults in aÂwurtzite GaAs nanowire by nanobeam X-ray diffraction. Journal of Synchrotron Radiation, 2017, 24, 981-990.	2.4	9
148	Two-dimensional electron gas at wurtziteâ€"zinc-blende InP interfaces induced by modulation doping. Applied Physics Letters, 2020, 116, 232103.	3.3	9
149	Magnetoresistance in Mn ion-implanted GaAs:Zn nanowires. Applied Physics Letters, 2014, 104, 153112.	3.3	8
150	Direct Observations of Twin Formation Dynamics in Binary Semiconductors. ACS Nanoscience Au, 2022, 2, 49-56.	4.8	8
151	A cathodoluminescence study of the influence of the seed particle preparation method on the optical properties of GaAs nanowires. Nanotechnology, 2012, 23, 265704.	2.6	7
152	High current density InAsSb/GaSb tunnel field effect transistors. , 2012, , .		7
153	Sn-seeded GaAs nanowires grown by MOVPE. Nanotechnology, 2016, 27, 215603.	2.6	7
154	Hybrid ZnO/GaN distributed Bragg reflectors grown by plasma-assisted molecular beam epitaxy. APL Materials, 2016, 4, 086106.	5.1	7
155	Radial band bending at wurtziteâ€"zinc-blendeâ€"GaAs interfaces. Nano Futures, 2018, 2, 035002.	2.2	7
156	Effect of Radius on Crystal Structure Selection in IIIâ€"V Nanowire Growth. Crystal Growth and Design, 2020, 20, 5373-5379.	3.0	7
157	Simulating Vaporâ€"Liquidâ€"Solid Growth of Au-Seeded InGaAs Nanowires. ACS Nanoscience Au, 2022, 2, 239-249.	4.8	7
158	Atomically sharp, crystal phase defined GaAs quantum dots. Applied Physics Letters, 2021, 119, .	3.3	7
159	Phonon Transport and Thermoelectricity in Defect-Engineered InAs Nanowires. Materials Research Society Symposia Proceedings, 2012, 1404, 36.	0.1	6
160	Micro-Raman spectroscopy for the detection of stacking fault density in InAs and GaAs nanowires. Physical Review B, 2017, 96, .	3.2	6
161	Spectroscopy and level detuning of few-electron spin states in parallel InAs quantum dots. Physical Review B, 2018, 98, .	3.2	6
162	Kinetic Engineering of Wurtzite and Zinc-Blende AlSb Shells on InAs Nanowires. Nano Letters, 2018, 18, 5775-5781.	9.1	6

#	Article	IF	Citations
163	Unraveling electronic band structure of narrow-bandgap pâ€“n nanojunctions in heterostructured nanowires. Physical Chemistry Chemical Physics, 2021, 23, 25019-25023.	2.8	6
164	Cu particle seeded InPâ€“InAs axial nanowire heterostructures. Physica Status Solidi - Rapid Research Letters, 2013, 7, 850-854.	2.4	5
165	Imaging Atomic Scale Dynamics on IIIâ€“V Nanowire Surfaces During Electrical Operation. Scientific Reports, 2017, 7, 12790.	3.3	5
166	Sb Incorporation in Wurtzite and Zinc Blende InAs_{1âˆ’}<i>_x</i>Sb<i>_x</i> Branches on InAs Template Nanowires. Small, 2018, 14, e1703785.	10.0	5
167	Understanding GaAs Nanowire Growth in the Agâ€“Au Seed Materials System. Crystal Growth and Design, 2018, 18, 6702-6712.	3.0	5
168	Growth selectivity control of InAs shells on crystal phase engineered GaAs nanowires. Nanoscale Advances, 2022, 4, 3330-3341.	4.6	5
169	Effects of Parity and Symmetry on the Aharonovâ€“Bohm Phase of a Quantum Ring. Nano Letters, 2022, 22, 334-339.	9.1	5
170	Measurements of light absorption efficiency in InSb nanowires. Structural Dynamics, 2014, 1, 014502.	2.3	4
171	Nanowire morphology and particle phase control by tuning the In concentration of the foreign metal nanoparticle. Nanotechnology, 2019, 30, 054005.	2.6	4
172	Symmetry-controlled singlet-triplet transition in a double-barrier quantum ring. Physical Review B, 2021, 104, .	3.2	4
173	Size-selected compound semiconductor quantum dots by nanoparticle conversion. Nanotechnology, 2007, 18, 105306.	2.6	3
174	Realization of single and double axial InSbâ€“GaSb heterostructure nanowires. Physica Status Solidi - Rapid Research Letters, 2014, 8, 269-273.	2.4	3
175	Self-selective formation of ordered 1D and 2D GaBi structures on wurtzite GaAs nanowire surfaces. Nature Communications, 2021, 12, 5990.	12.8	3
176	Post-nucleation evolution of the liquidâ€“solid interface in nanowire growth. Nanotechnology, 2022, 33, 105607.	2.6	3
177	Selective tuning of spin-orbital Kondo contributions in parallel-coupled quantum dots. Physical Review B, 2020, 101, .	3.2	2
178	Time-resolved photoluminescence studies of single interface wurtzite/zincblende heterostructured InP nanowires. Applied Physics Letters, 2022, 120, .	3.3	2
179	Gate control, g factors, and spin-orbit energy of p -type GaSb nanowire quantum dot devices. Physical Review B, 2021, 103, .	3.2	1
180	Non-resonant Raman scattering of wurtzite GaAs and InP nanowires. Optics Express, 2020, 28, 11016.	3.4	1

#	Article	IF	Citations
181	Introduction to the Issue on Nanowires. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 763-765.	2.9	0
182	Measuring Surface Tension of III-V Nanowire Au-Catalyst Droplets with an E-field. Microscopy and Microanalysis, 2021, 27, 27-28.	0.4	0